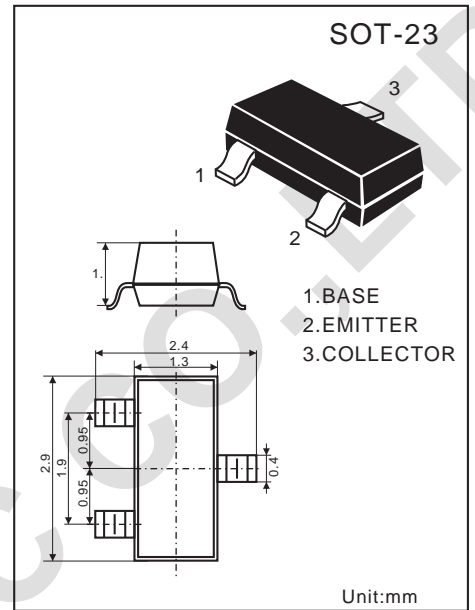
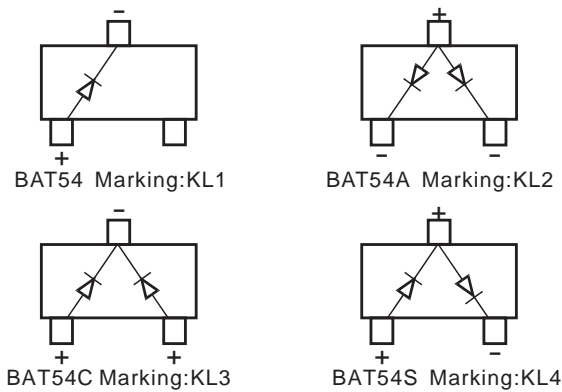


## SCHOTTKY DIODE

### Features

- Power dissipation  
 $P_D : 200 \text{ mW} (T_{amb}=25^\circ \text{C})$
- Pluse Drain  
 $I_F : 200 \text{ mA}$
- Reverse Voltage  
 $V_R : 30\text{V}$
- Operating and storage junction temperature range  
 $T_j, T_{stg} : -55^\circ \text{C} \text{ to } +150^\circ \text{C}$



### Electro-Optical Characteristics

( $T_a=25^\circ \text{C}$ )

Parameter	Symbol	Test Condition	MIN.	MAX.	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	30		V
Reverse Voltage leakage current	$I_R$	$V_R=75\text{V}$		2	$\mu\text{A}$
Forward Voltage	$V_F$	$I_F=0.1\text{mA}$ $I_F=1\text{mA}$ $I_F=10\text{mA}$ $I_F=30\text{mA}$ $I_F=100\text{mA}$		240 320 400 500 1000	mV
Diode Capacitance	$C_D$	$V_R=1\text{V}$ $f=1\text{MHz}$		10	pF
Reverse Recovery Time	$t_{rr}$	$I_F=10\text{mA}$ though $I_R=10\text{mA}$ to $I_R=1.0\text{mA}$ $RC=100\Omega$		5	nS

